

## ISL70040SEH

Total Dose Test

TR060  
Rev.0.00  
Jan 15, 2018

## Introduction

This report documents the results of low and high dose rate total dose testing and subsequent high temperature biased annealing of the ISL70040SEH GaN FET driver. The tests were conducted to provide an assessment of the total dose hardness of the part and to provide an estimate of dose rate, bias, or anneal sensitivity. Parts were irradiated under bias and with all pins grounded at low and at high dose rate. The ISL70040SEH is rated at 100krad(Si) at high dose rate (50-300rad(Si)/s) and at 75krad(Si) at low dose rate (0.01rad(Si)/s) and is acceptance tested on a wafer-by-wafer basis to its SMD limits.

## Product Description

The ISL70040SEH is a low side driver designed to drive enhancement mode gallium nitride (eGaN) power FET devices. The part operates over a supply voltage range from 4.5V to 13.2V and offers both inverting (INB) and non-inverting (IN) inputs to satisfy requirements for inverting and non-inverting gate drive with a single device. The ISL70040SEH supplies 4.5V gate drive voltage ( $V_{DRV}$ ) that is generated using an internal regulator, which prevents the driven device's gate voltage exceeding its maximum gate-source rating. The gate drive voltage also features Undervoltage Lockout (UVLO) protection that ignores the inputs (IN/INB) and keeps OUTL turned on to ensure the GaN FET is in an OFF state whenever  $V_{DRV}$  is below the UVLO threshold. The inputs of the ISL70040SEH can withstand voltages up to 14.7V. The split outputs of the ISL70040SEH offer the flexibility to adjust the turn-on and turn-off speed independently by adding impedance in the turn-on and turn-off paths.

The ISL70040SEH operates across the -55°C to +125°C temperature range and is offered in an 8 Ld hermetically sealed ceramic Surface Mount Device (SMD) package or in die form. The part is implemented in the Renesas P6 power management and mixed signal process, a junction-isolated 5V BiCMOS flow with added high voltage DMOS devices. The fabrication process is QML certified and is in volume commercial production.

## Related Literature

- MIL-STD-883 Test Method 1019
- For a full list of related documents, visit our website
  - [ISL70040SEH](#) product page

## 1. Test Description

### 1.1 Irradiation Facilities

High dose rate testing was performed at 187rad(Si)/s using a Gammacell 220 gamma ray irradiator located in the Palm Bay, Florida facility. Low dose rate testing was performed at 0.01rad(Si)/s using the Palm Bay Hopewell Designs N40 panoramic gamma ray irradiator. Biased irradiation and annealing were performed on all samples following irradiation, using the Appendix bias configuration at +100°C for 168 hours in a small temperature chamber.

### 1.2 Test Fixturing

[“Appendix” on page 15](#) shows the configuration used for biased irradiation at both dose rates.

### 1.3 Characterization Equipment and Procedures

All electrical testing was performed at room temperature outside the irradiator, using production Automated Test Equipment (ATE) with datalogging to SMD 5962-17233 limits at each downpoint.

### 1.4 Experimental Matrix

Irradiation was performed in accordance with the guidelines of MIL-STD-883 Test Method 1019. The experimental matrix consisted of 12 samples irradiated at low dose rate under bias, 12 samples irradiated at low dose rate with all pins grounded, 12 samples irradiated at high dose rate under bias, and 12 samples irradiated at high dose rate with all pins grounded. Three control units were used.

The ISL70040SEH samples were drawn from wafer lot 5VAFB. All samples were packaged in the hermetic 6mm x 6mm 8 Ld surface mount package (package code J8.A). Samples were processed through the standard burn-in cycle before irradiation.

### 1.5 Downpoints

Downpoints for the low dose rate tests were 0, 10, 30, 50, and 75krad(Si). Downpoints for the high dose rate tests were 0, 30, 50, 100, and 150krad(Si). All irradiations were followed by a high temperature biased anneal at +100°C.

## 2. Test Results

### 2.1 Attributes Data

Part	Dose Rate, rad(Si)/s	Bias	Sample Size	Downpoint	Pass (Note 1)	Fail
ISL70040SEH	0.01	Appendix	12	Pre-irradiation	12	0
				10krad(Si)	12	0
				30krad(Si)	12	0
				50krad(Si)	12	0
				75krad(Si)	12	0
				Anneal	12	0
ISL70040SEH	0.01	Grounded	12	Pre-irradiation	12	
				10krad(Si)	12	0
				30krad(Si)	12	0
				50krad(Si)	12	0
				75krad(Si)	12	0
				Anneal	12	0
ISL70040SEH	187	Appendix	12	Pre-irradiation	12	
				30krad(Si)	12	0
				50krad(Si)	12	0
				100krad(Si)	12	0
				150krad(Si)	12	0
				Anneal	12	0
ISL70040SEH	187	Grounded	12	Pre-irradiation	12	
				30krad(Si)	12	0
				50krad(Si)	12	0
				100krad(Si)	12	0
				150krad(Si)	12	0
				Anneal	12	0

Note:

1. 'Pass' indicates a sample that passes all pre- and post-irradiation SMD limits.

### 2.2 Critical Parameter Listing

[Table 1](#) lists 17 critical parameters that are considered indicative of part performance. These parameters are discussed in detail below, including the SMD parameter names for clarity, and are plotted in [Figures 1](#) through [17](#). All parametric limits are in accordance the ISL70040SEH SMD pre- and post-irradiation limits, which are identical.

**Table 1. Critical Parameters**

Figure	Parameter	Limit, Low	Limit, High	Units	Notes
<a href="#">1</a>	Quiescent power supply current	-	2.5	mA	4.5V supply
		-	2.5	mA	13.2V supply
<a href="#">2</a>	Operating supply current	-	13.0	mA	4.5V supply, 500kHz
		-	15.0	mA	13.2V supply, 500kHz

Table 1. Critical Parameters

Figure	Parameter	Limit, Low	Limit, High	Units	Notes
<a href="#">3</a>	Output voltage	4.29	-	V	4.5V supply
		4.34	4.71	V	13.2V supply
<a href="#">4</a>	Input HIGH level threshold	-	2.0	V	4.5V supply
		-	2.0	V	13.2V supply
<a href="#">5</a>	Input LOW level threshold	1.0	-	V	4.5V supply
		1.0	-	V	13.2V supply
<a href="#">6</a>	Input B HIGH level threshold	-	2.0	V	4.5V supply
		-	2.0	V	13.2V supply
<a href="#">7</a>	Input B LOW level threshold	1.0	-	V	4.5V supply
		1.0	-	V	13.2V supply
<a href="#">8</a>	Output rise time	21	90	ns	CL = 10,000pF
<a href="#">9</a>	Output fall time	16	50	ns	CL = 10,000pF
<a href="#">10</a>	Input to output turn-on propagation delay	15	65	ns	CL = 1,000pF
<a href="#">11</a>	Input to output turn-off propagation delay	15	65	ns	CL = 1,000pF
<a href="#">12</a>	Input B to output turn-on propagation delay	15	65	ns	CL = 1,000pF
<a href="#">13</a>	Input B to output turn-off propagation delay	15	65	ns	CL = 1,000pF
<a href="#">14</a>	Input to output propagation delay match	-8	8	ns	
<a href="#">15</a>	Input B to output propagation delay match	-8	8	ns	
<a href="#">16</a>	Driver output resistance	-	3.2	$\Omega$	IOUTH = 45mA
<a href="#">17</a>	Driver output resistance	-	1.0	$\Omega$	OOUTH = V <sub>DRV</sub> , IOU <sub>TL</sub> = -45mA
		-	3.0	$\Omega$	OOUTH = OOUTL, IOU <sub>TL</sub> = -45mA

[Figure 1](#) plots the quiescent power supply current ( $I_{DDQ}$ ) for the 4.5V supply and 13.2V supply cases.

[Figure 2](#) plots the operating power supply current ( $I_{DDO}$ ) for the 4.5V supply and 13.2V supply cases.

[Figure 3](#) plots the output voltage ( $V_{DRV}$ ) for the 4.5V supply and 13.2V supply cases.

[Figures 4](#) and [5](#) plot the input HIGH and LOW ( $V_{IH}$  and  $V_{IL}$ ) logic threshold voltages for the 4.5V supply and 13.2V supply cases.

[Figures 6](#) and [7](#) plot the input B HIGH and LOW ( $V_{IH}$  and  $V_{IL}$ ) logic threshold voltages for the 4.5V supply and 13.2V supply cases.

[Figures 8](#) and [9](#) plot the 10% to 90% output rise and fall time ( $t_{RISE}$  and  $t_{FALL}$ ) with a 10nF load capacitance.

[Figures 10](#) and [11](#) plot the input to output turn-on and turn-off propagation delays ( $t_{DON}$  and  $t_{DOFF}$ ).

[Figures 12](#) and [13](#) plot the input B to output turn-on and turn-off propagation delays ( $t_{DON}$  and  $t_{DOFF}$ ).

[Figure 14](#) plots the input to output turn-on and turn-off propagation delay match ( $t_{DM}$ ).

[Figure 15](#) plots the input B to output turn-on and turn-off propagation delay match ( $t_{DM}$ ).

[Figure 16](#) plots the driver output resistance ( $r_{ONP}$ ) with the HIGH output current at 45mA.

[Figure 17](#) plots the driver output resistance ( $r_{ONN}$ ) with the HIGH output at  $V_{DRV}$  and the HIGH output at the LOW output cases, both with the LOW output current at -45mA.

### 2.3 Critical Parameter Variables Data

The plots in [Figures 1](#) through [17](#) show the TID response of the critical parameters outlined in [“Critical Parameter Listing”](#) on [page 3](#). The figures plot the average only because the data was tightly grouped.

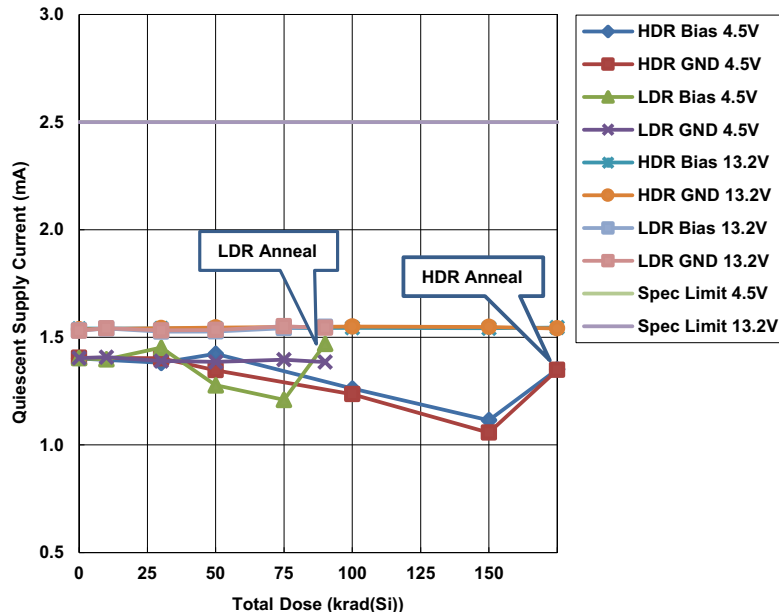


Figure 1. ISL70040SEH quiescent power supply current ( $I_{DDQ}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal; the LDR anneal was performed after 75krad(Si) at low dose rate while the HDR anneal was performed after 150krad(Si) at high dose rate. The sample size of all cells was 12. The SMD limit is 2.5mA maximum (4.5V supply and 13.2V supply).

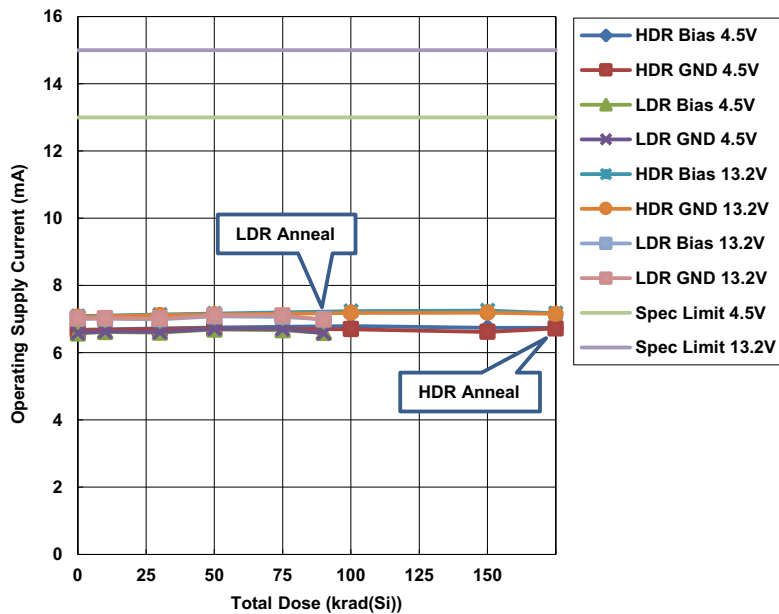


Figure 2. ISL70040SEH operating (500kHz) power supply current ( $I_{DDQ}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 13mA maximum (4.5V supply) and 15mA maximum (13.2V supply).

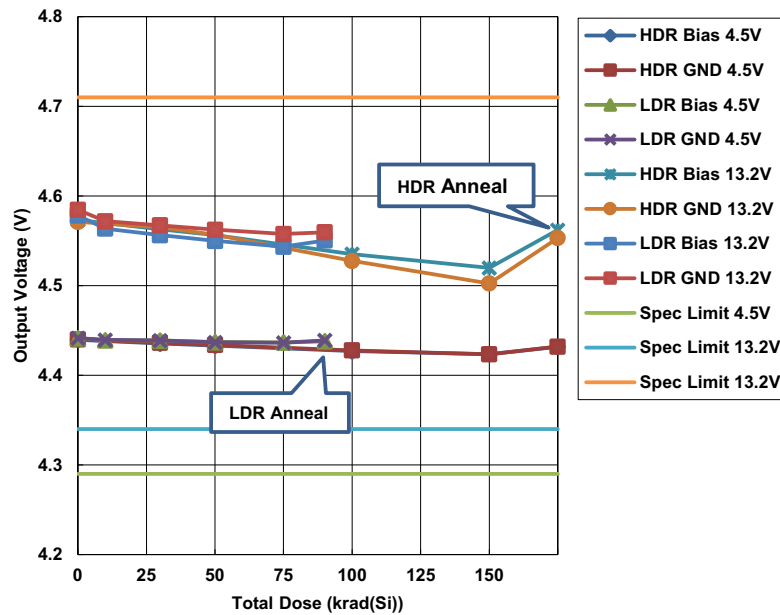


Figure 3. ISL70040SEH output voltage ( $V_{DRV}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 4.29V minimum (4.5V supply) and 4.34V to 4.71V (13.2V supply).

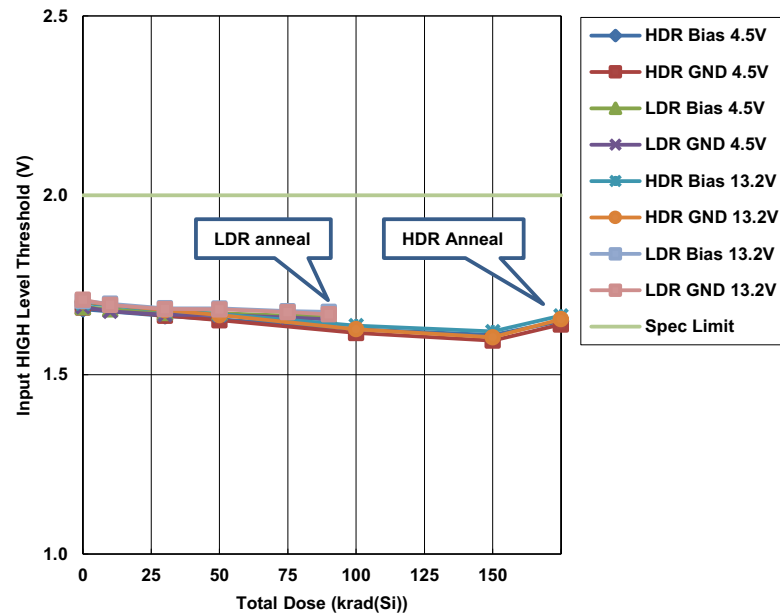


Figure 4. ISL70040SEH input HIGH level threshold ( $V_{IH}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limit is 2.0V maximum (4.5V supply and 13.2V supply).

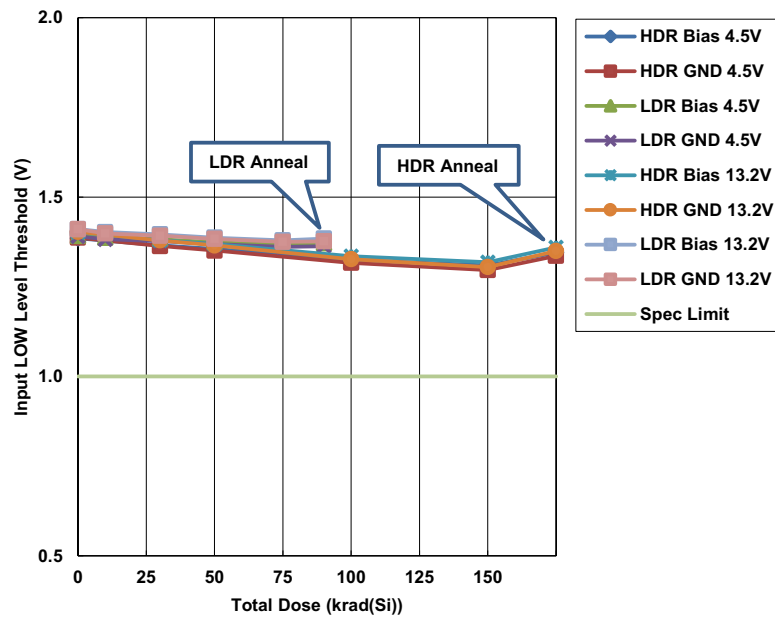


Figure 5. ISL70040SEH input LOW level threshold ( $V_{IL}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 1.0V minimum (4.5V supply and 13.2V supply).

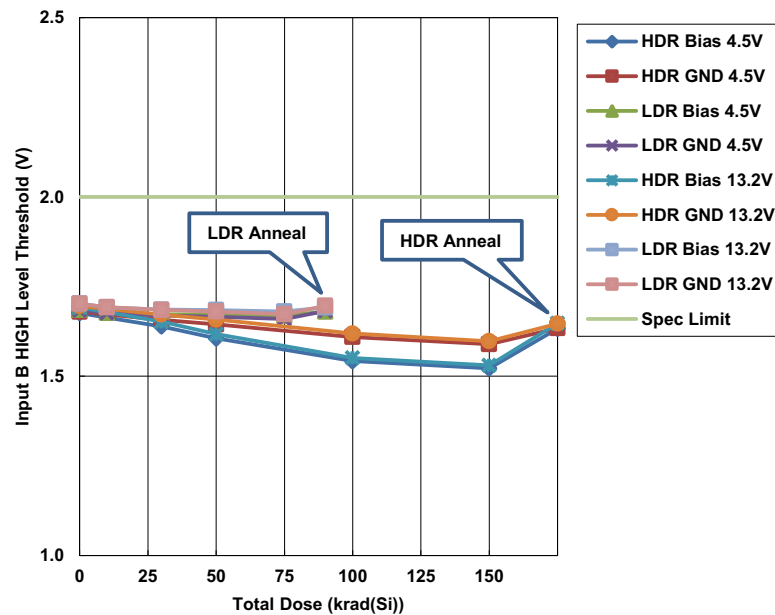


Figure 6. ISL70040SEH input B HIGH level threshold ( $V_{IH}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limit is 2.0V maximum (4.5V supply and 13.2V supply).

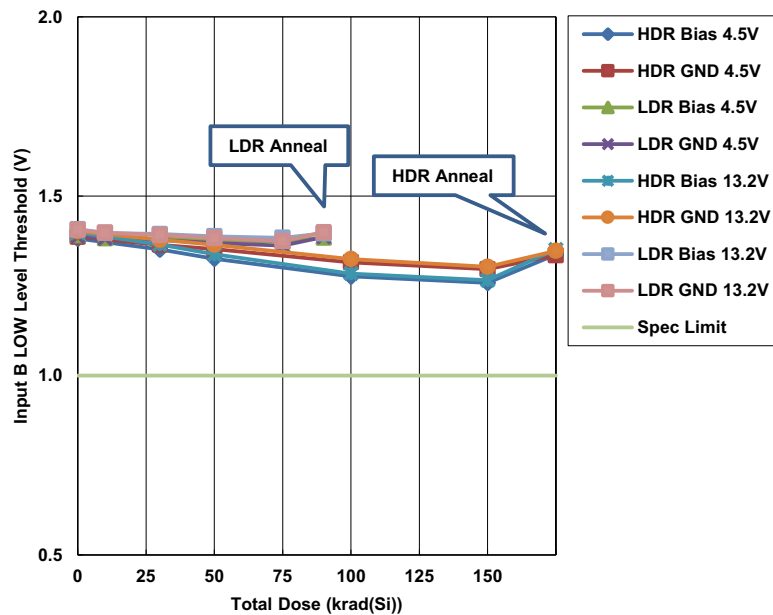


Figure 7. ISL70040SEH input B LOW level threshold ( $V_{IL}$ ), 4.5V and 13.2 V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limit is 1.0V minimum (4.5V supply and 13.2V supply).

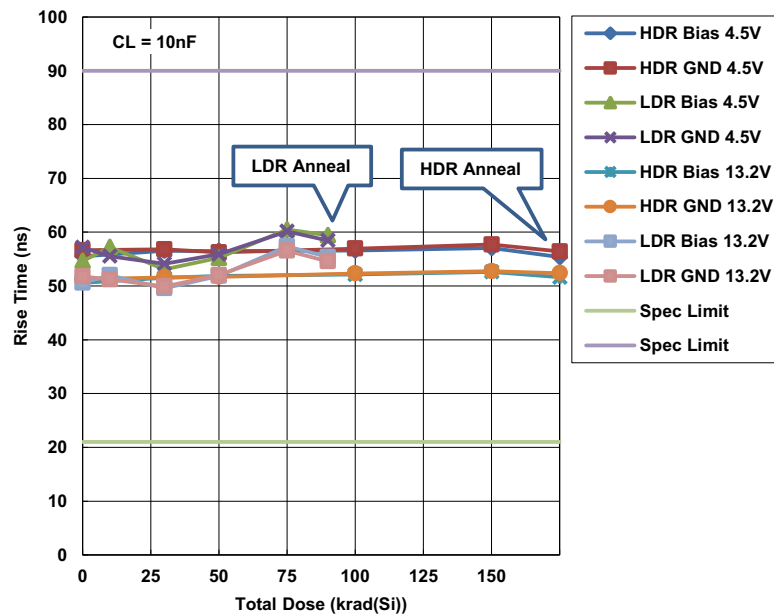


Figure 8. ISL70040SEH rise time ( $t_{RISE}$ ) as a function of total dose irradiation at low and at high dose rate, 10nF load capacitance, for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 21ns to 90ns.



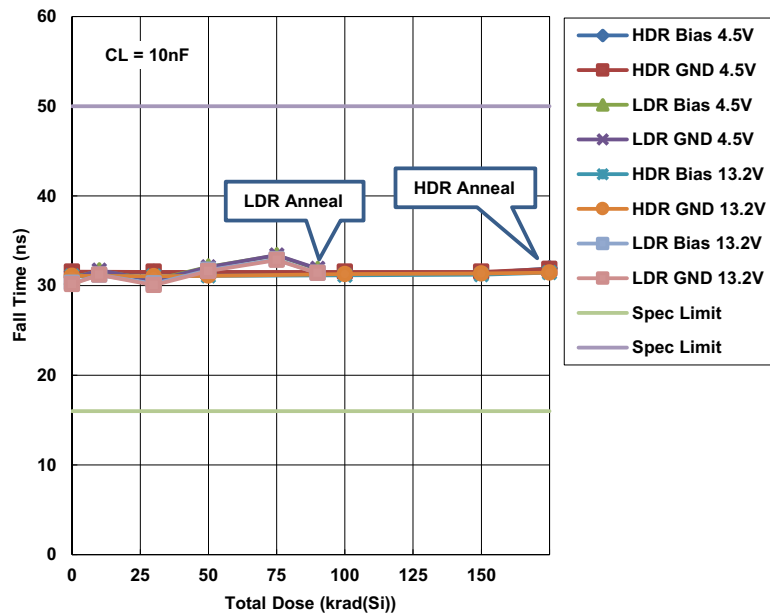


Figure 9. ISL70040SEH fall time ( $t_{FALL}$ ) as a function of total dose irradiation at low and at high dose rate, 10nF load capacitance, for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 16ns to 50ns.

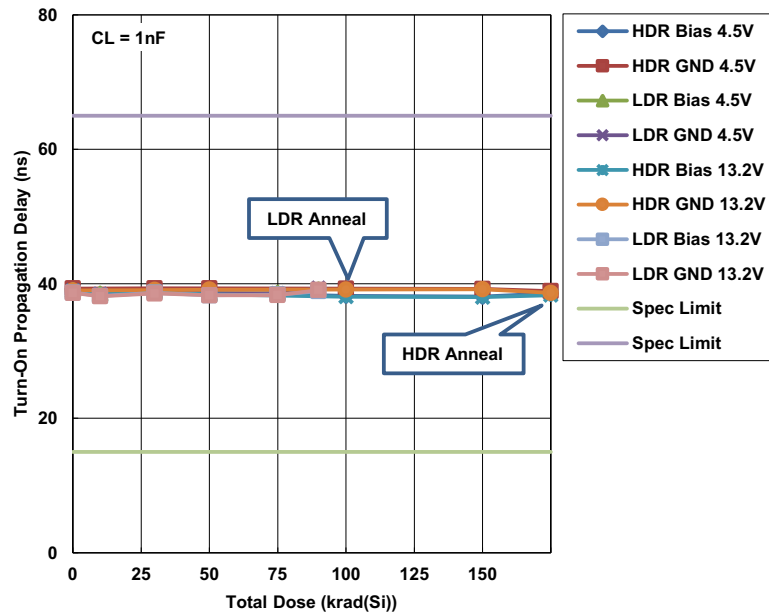


Figure 10. ISL70040SEH input to output turn-on propagation delay ( $t_{DON}$ ), 4.5V and 13.2V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 15ns to 65ns.

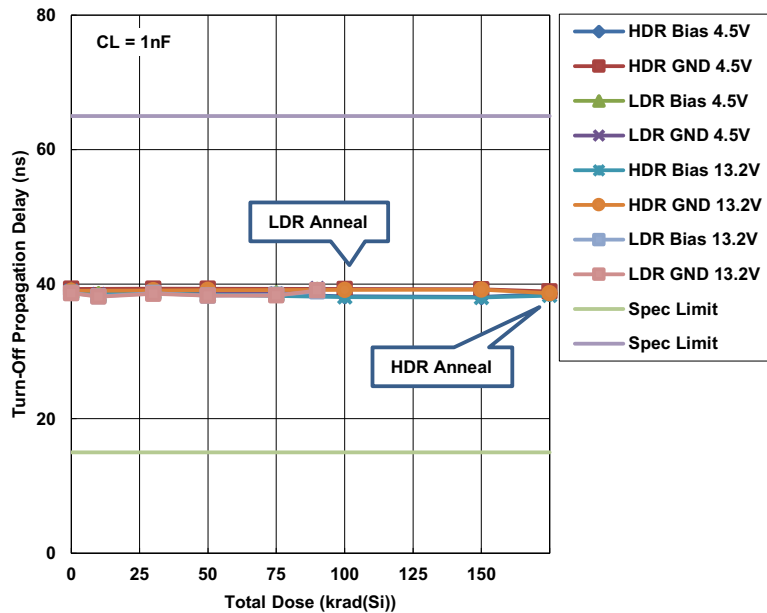


Figure 11. ISL70040SEH input to output turn-off propagation delay ( $t_{DOFF}$ ), 4.5V and 13.2V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 15ns to 65ns.

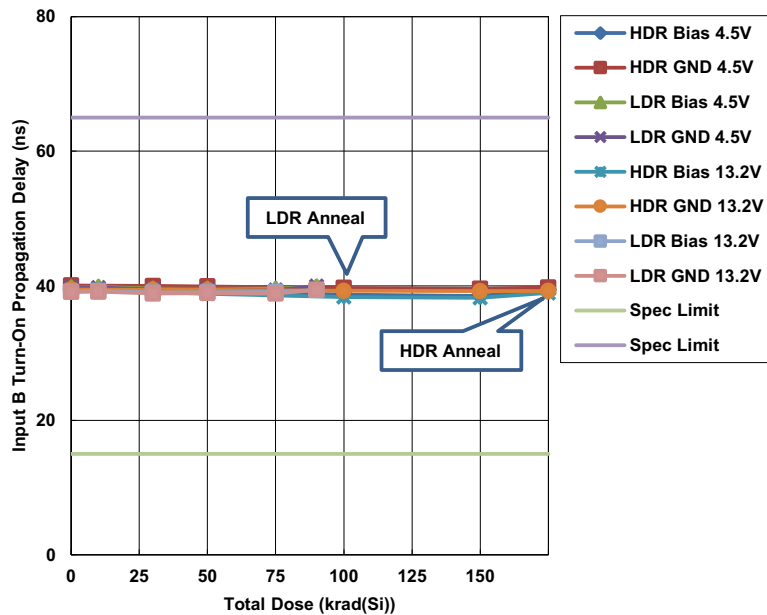


Figure 12. ISL70040SEH input B to output turn-on propagation delay ( $t_{DON}$ ), 4.5V and 13.2V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 15ns to 65ns.

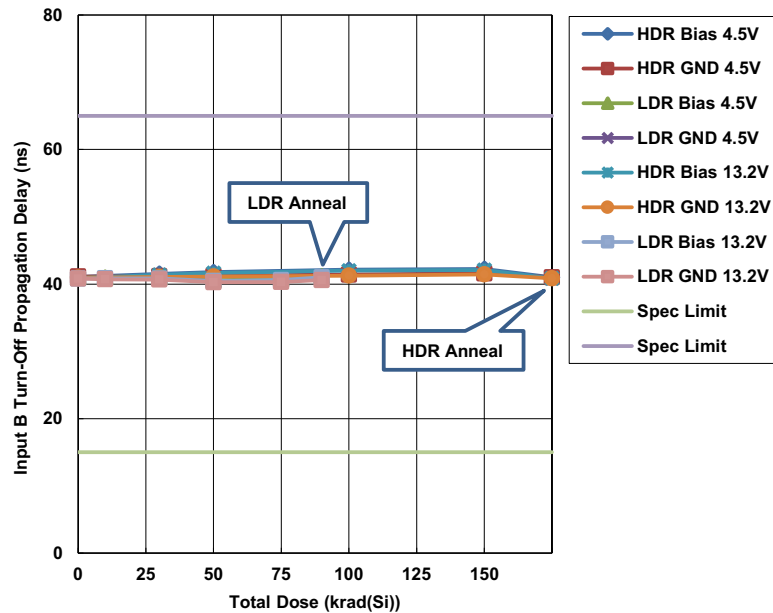


Figure 13. ISL70040SEH input B to output turn-off propagation delay ( $t_{DOFF}$ ), 4.5V and 13.2V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 15ns to 65ns.

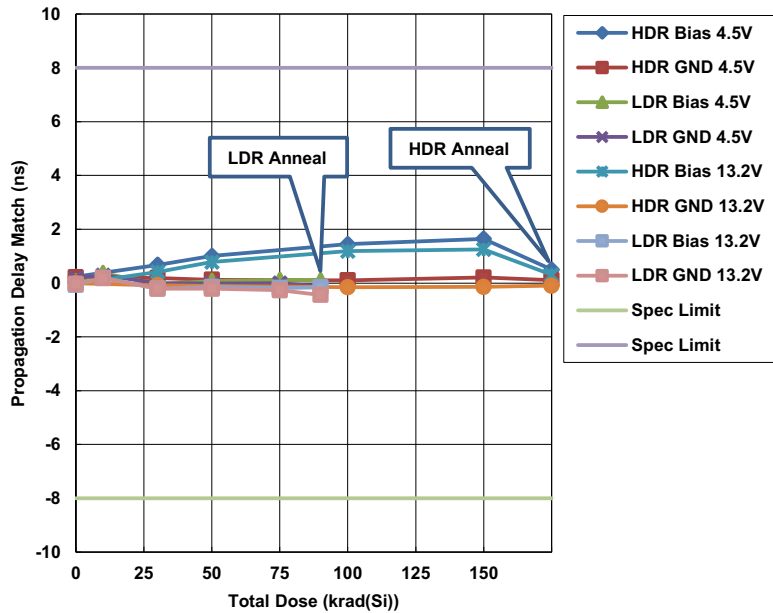


Figure 14. ISL70040SEH input to output propagation delay match ( $t_{DM}$ ), 4.5V and 13.2V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are -8ns to 8ns.

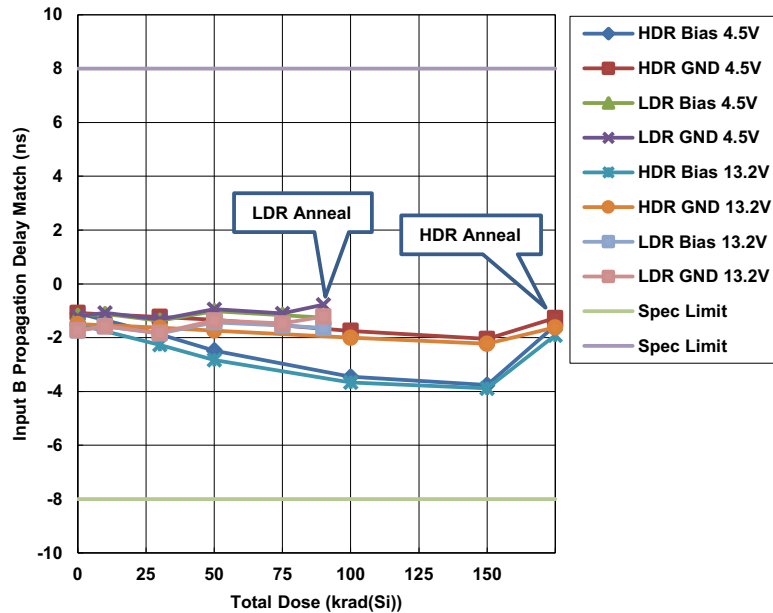


Figure 15. ISL70040SEH input B to output propagation delay match ( $t_{DM}$ ), 4.5V and 13.2V supply, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are -8ns to 8ns.

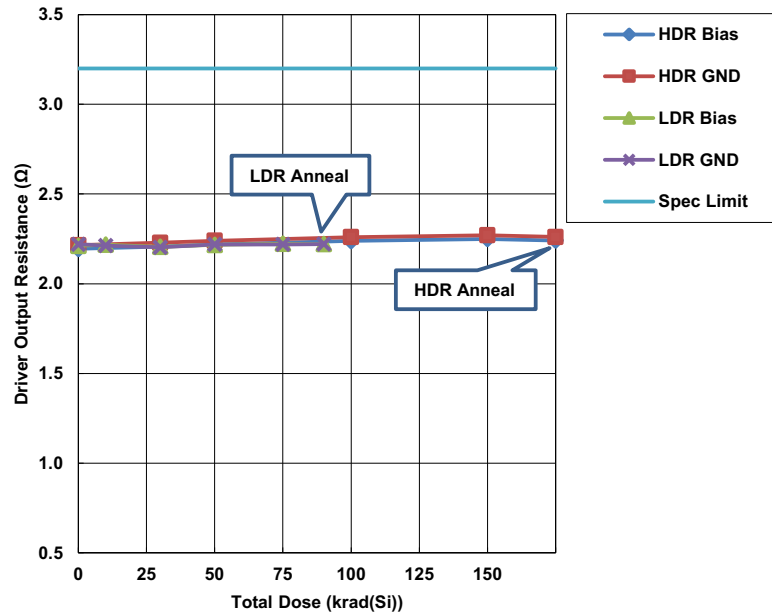


Figure 16. ISL70040SEH driver output resistance ( $r_{ONP}$ ), output HIGH current 45mA, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limit is 3.2Ω maximum.

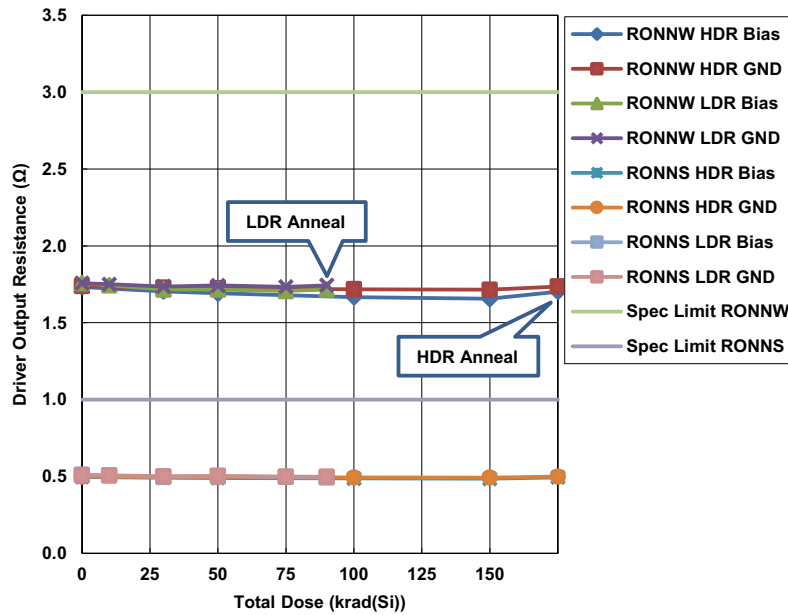


Figure 17. ISL70040SEH driver output resistance ( $r_{ONN}$ ), output LOW current -45mA, HIGH output at  $V_{DRV}$  and at OUTL cases, as a function of total dose irradiation at low and at high dose rate for the biased (per Appendix) and unbiased (all pins grounded) cases, plotting the average. The low dose rate was 0.01rad(Si)/s and the high dose rate was 187rad(Si)/s. The irradiations were followed by a +100°C 168-hour biased anneal. The sample size of all cells was 12. The SMD limits are 1.0Ω maximum (OUTH =  $V_{DRV}$ ) and 3.0Ω (OUTH = OUTL).

### 3. Discussion and Conclusion

The results of a low and high dose rate biased and grounded total dose test of the ISL70040SEH radiation tolerant low side GaN FET driver were reported. All irradiations were followed by a 168-hour anneal at +100°C under bias. [“Attributes Data” on page 3](#) summarizes the attributes data for the test. [“Critical Parameter Listing” on page 3](#) summarizes the 17 critical parameters for the part. Finally, [“Critical Parameter Variables Data” on page 5](#) provides the plots of the total dose and anneal response for these critical parameters.

All parameters remained well within the SMD limits at all downpoints and showed no differences in total dose response between low and high dose rate or between biased and unbiased irradiation. This leads to the conclusion that the part is not dose rate or bias sensitive.

## 4. Appendix

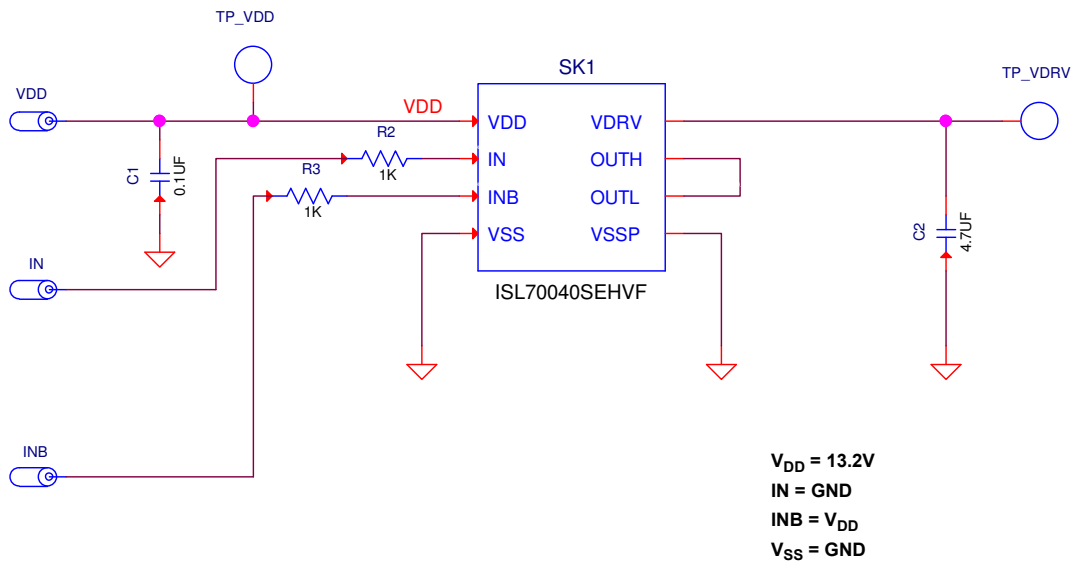


Figure 18. ISL70040SEH Irradiation and Anneal Bias Configuration

## 5. Revision History

Rev.	Date	Description
0.00	Jan 15, 2018	Initial release



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**Renesas Electronics America Inc.**  
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.  
Tel: +1-408-432-8888, Fax: +1-408-434-5351

**Renesas Electronics Canada Limited**  
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3  
Tel: +1-905-237-2004

**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K  
Tel: +44-1628-651-700, Fax: +44-1628-651-804

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
Room 1709 Quantum Plaza, No.27 ZhichunLu, Haidian District, Beijing, 100191 P. R. China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, 200333 P. R. China  
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2265-6688, Fax: +852-2886-9022

**Renesas Electronics Taiwan Co., Ltd.**  
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan  
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

**Renesas Electronics Singapore Pte. Ltd.**  
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949  
Tel: +65-6213-0200, Fax: +65-6213-0300

**Renesas Electronics Malaysia Sdn.Bhd.**  
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

**Renesas Electronics India Pvt. Ltd.**  
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India  
Tel: +91-80-67208700, Fax: +91-80-67208777

**Renesas Electronics Korea Co., Ltd.**  
17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea  
Tel: +82-2-558-3737, Fax: +82-2-558-5338